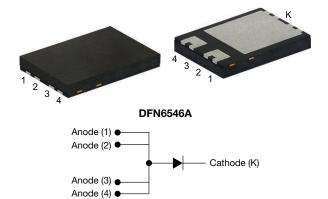
**Vishay Semiconductors** 

## Ultrafast Rectifier, 8 A FRED Pt<sup>®</sup>



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## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	8 A				
V <sub>R</sub>	200 V				
V <sub>F</sub> at I <sub>F</sub>	0.75 V				
t <sub>rr</sub> (typ.)	15 ns				
I <sub>FSM</sub>	131 A				
T <sub>J</sub> max.	175 °C				
Package	DFN6546A				
Circuit configuration	Single				

### **FEATURES**

- · Very low profile typical height of 0.88 mm
- · Ideal for automated placement
- Wettable flanks allows easy inspection with AOI (automated optical inspection). No X-ray necessary
- · Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **TYPICAL APPLICATIONS**

For use in high frequency inverters, DC/DC converters, freewheeling diodes, clamping and snubber, polarity protection, and LED lighting

#### **MECHANICAL DATA**

#### Case: DFN6546A

Molding compound meets UL 94 V-0 flammability rating Terminals: matte tin plated leads, solderable per J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>M</sub> = 156 °C, D = 0.50	8	•		
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_J = 25 \text{ °C}, 10 \text{ ms} \text{ sine pulse}$	131	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage	V	I <sub>F</sub> = 8 A	-	0.95	1.1	V	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	0.75	0.85		
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	1		
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	150	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	24	-	pF	

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX				MAX.	UNITS	
		I <sub>F</sub> = 0.5 A, I <sub>R</sub> =	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A			25		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	13	-	ns A	
		T <sub>J</sub> = 125 °C		-	22	-		
Peak recovery current	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 8 A, dI <sub>F</sub> /dt = 500 A/μs, V <sub>R</sub> = 200 V	-	4.3	-		
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	8.0	-		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	32	-	nC	
		T <sub>J</sub> = 125 °C		-	93	-		

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C		
Thermal resistance, junction to mount	R <sub>thJM</sub> <sup>(1)</sup>		-	-	2.6	°C/W		
Weight			-	0.086	-	9		
Marking device		Case style DFN6546A	8H2					

Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)

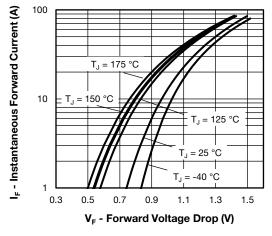


Fig. 1 - Typical Forward Voltage Drop Characteristics

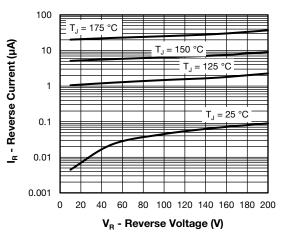


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

## VS-8ERH02-M3

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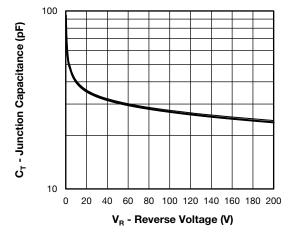


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

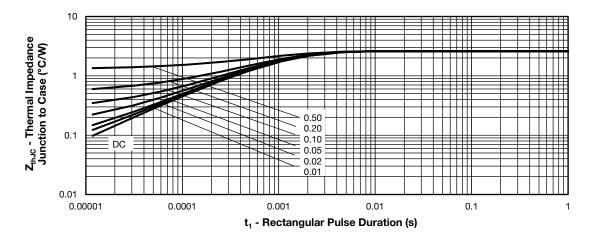
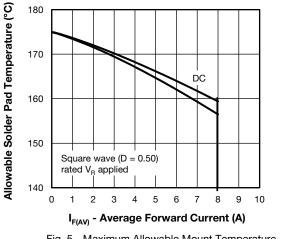
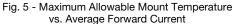


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount





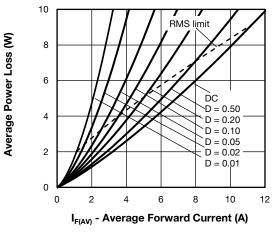


Fig. 6 - Forward Power Loss Characteristics

#### Note

 $\begin{array}{l} \mbox{Formula used: } T_M = T_J - (Pd + Pd_{REV}) \ x \ R_{thJM}; \\ \mbox{Pd} = \mbox{forward power loss} = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 5); \\ \mbox{Pd}_{REV} = \ inverse \ power \ loss = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ at \ V_{R1} = \ rated \ V_R \end{array}$ 

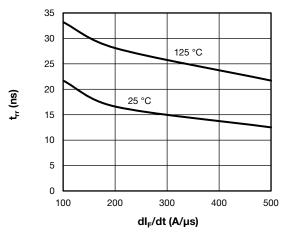
Revision: 19-May-2025

3

Document Number: 97363

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Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

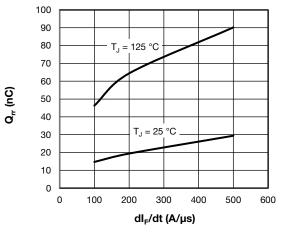


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

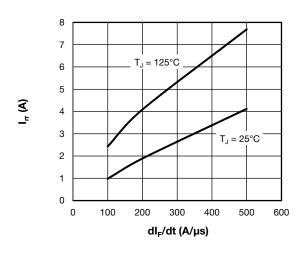


Fig. 9 - I<sub>rr</sub> vs. dl/dt

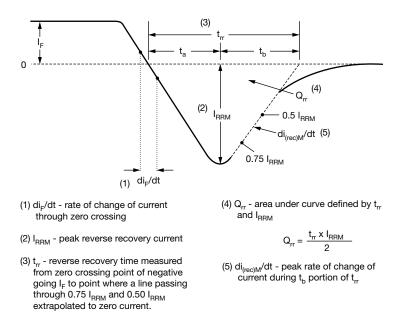


Fig. 10 - Reverse Recovery Waveform and Definitions

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### **ORDERING INFORMATION TABLE**

Device code	vs-	8	Е	R	н	02	-M3
Device code	V3-	0			п	02	-1013
	1	2	3	4	5	6	7
	1	- Visl	nay Sen	nicondu	ctors pr	oduct	
	2	- Cur	rent rati	ng (8 =	8 A)		
	3 -	- Circ	cuit con	figuratio	n:		
		E =	single c	liode			
	4	• R =	DFN65	46A pac	kage		
	5 -	- Pro	cess typ	be,			
		H =	ultrafas	st recove	ery		
	6	- Vol	tage coo	de (02 =	200 V)		
	7.	M3	3 = halo	gen-free	e, RoHS	-compli	iant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N PREFERRED PACKAGE CODE BASE QUANTITY PACKAGING DESCRIPTION							
VS-8ERH02-M3/I	I	6000	13" diameter plastic tape and reel				

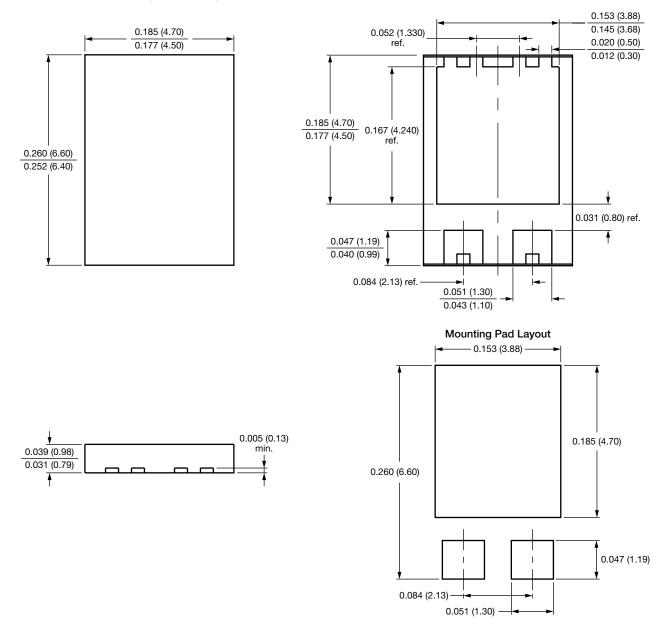
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?97347				
Part marking information	www.vishay.com/doc?97348				
Packaging information	www.vishay.com/doc?98691				

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# DFN6456, FRED Pt®

#### **DIMENSIONS** in inches (millimeters)





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1